

# 1.42mm Silicon PD Chip datasheet

P/N : WS56-01C

## Feature

Si PIN photodiode chip

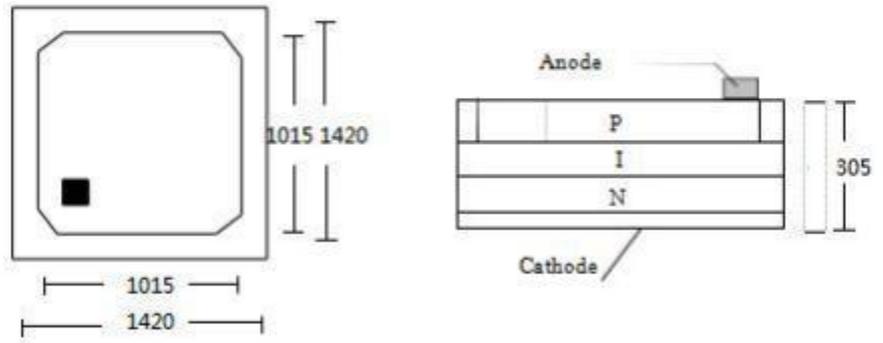
## Structure

Planar type : PIN diode

Electrodes :

Back side ( Cathode ) : Au alloy

Top side (Anode) : Al



## DIMENSIONS

Conditions	Typ.			Unit
Active	1015±20 x 1015±20			μm
Chip width	1420			μm
Chip length	1420			μm
Chip height	285	305	325	μm
Pad Area	160 x 160			μm

## Electro-Optical Characteristics ( @ Ta =25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Forward Voltage	Vf	If=10mA, H=0	0.5		1.3	V
Reverse Voltage	Vbr	Ir=100μA, H=0	35			V
Reverse Dark Current	Id	Vr=10V			1	nA
Sensitive Wavelength Peak	λp		400	940	1100	nm
Capacitance	Cj	VR=3V, f=1MHz		11		pF